# PT2302B

20V N-Channel Enhancement Mode MOSFET

**VDS= 20V**

**RDS(ON), Vgs@ 4.5V, Ids@ 2.0A** ＜50mΩ

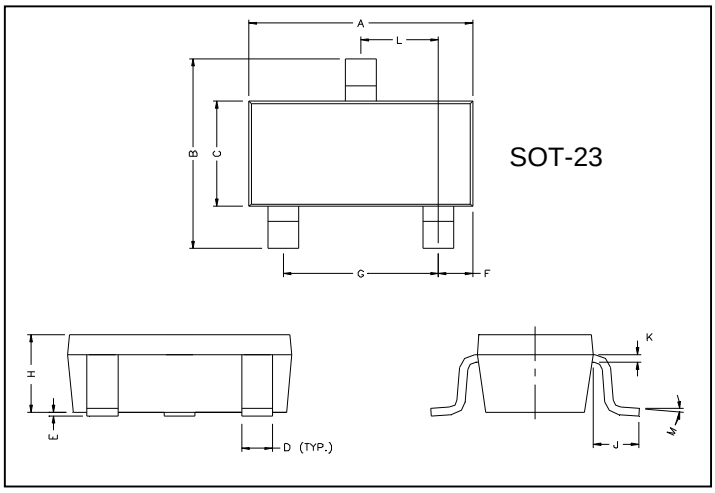
**RDS(ON), Vgs@ 2.5V, Ids@ 1.0A** ＜80mΩ

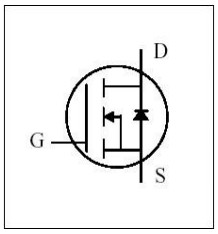
**Features**

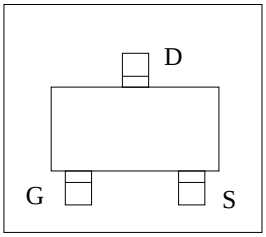
Advanced trench process technology

High Density Cell Design For Ultra Low On-Resistance

Package Dimensions




| REF. | Millimeter | | REF. | Millimete | |
|---|---|---|---|---|---|
| | Min. | Max. | | Min. | Max. |
| A | 2.80 | 3.00 | G | 1.80 | 2.00 |
| B | 2.30 | 2.50 | H | 0.90 | 1.1 |
| C | 1.20 | 1.40 | K | 0.10 | 0.20 |
| D | 0.30 | 0.50 | J | 0.35 | 0.70 |
| E | 0 | 0.10 | L | 0.92 | 0.98 |
| F | 0.45 | 0.55 | M | 0° | 10° |

Maximum Ratings and Thermal Characteristics (TA = 25oC unless otherwise noted)

| **Parameter** | **Symbol** | **Limit** | **Unit** |
|---|---|---|---|
| Drain-Source Voltage | $V_{DS}$ | 20 | V |
| Gate-Source Voltage | $V_{GS}$ | ±12 | |
| Continuous Drain Current | $I_D$ | 2.3 | A |
| Pulsed Drain Current [1] | $I_{DM}$ | 6 | |
| Maximum Power Dissipation [2] | $P_D$ | 0.6 | W |
| Operating Junction and Storage Temperature Range | $T_J$, $T_{stg}$ | -55 to 150 | °C |

Notes

1) Pulse width limited by maximum junction temperature.

2) Surface Mounted on FR4 Board, t ≤ 5 sec.

## ELECTRICAL CHARACTERISTICS

| **Parameter** | Symbol | **Test Condition** | Min. | Typ. | Miax. | Unit |
|---|---|---|---|---|---|---|
| **Static** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | $V_{GS}$ = 0V, $I_D$ = 250uA | 20 | | | V |
| Drain-Source On-State Resistance[1)] | $R_{DS(on)}$ | $V_{GS}$ = 4.5V, $I_D$ = 2A | | | 50 | mΩ |
| | | $V_{GS}$ = 2.5V, $I_D$ = 1A | | | 80 | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ =$V_{GS}$, $I_D$ = 250uA | 0.6 | | 1.1 | V |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 19.5V, $V_{GS}$ = 0V | | | 1 | uA |
| Gate Body Leakage | $I_{GSS}$ | $V_{GS}$ =12V, $V_{DS}$ = 0V | | | 100 | nA |
| Forward Transconductance[1)] | $g_{fs}$ | $V_{DS}$ = 5V, $I_D$ = 2.3A | | 10 | — | S |
| **Dynamic** | | | | | | |
| Total Gate Charge | $Q_g$ | $V_{DS}$ = 10V, $I_D$ = 2.3A<br>$V_{GS}$ = 4.5V | | 5.4 | | nC |
| Gate-Source Charge | $Q_{gs}$ | | | 0.65 | | |
| Gate-Drain Charge | $Q_{gd}$ | | | 1.6 | | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = 10V, RL=5.5Ω<br>$I_D$ ≅ 2.3A,$V_{GEN}$ = 4.5V<br>$R_G$ = 6Ω | | 12 | | ns |
| Turn-On Rise Time | $t_r$ | | | 36 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 34 | | |
| Turn-Off Fall Time | $t_f$ | | | 10 | | |
| Input Capacitance | $C_{iss}$ | $V_{DS}$ = 10V, $V_{GS}$ = 0V<br>f = 1.0 MHz | | 340 | | pF |
| Output Capacitance | $C_{oss}$ | | | 115 | | |
| Reverse Transfer Capacitance | $C_{rss}$ | | | 33 | | |
| Diode Forward Voltage | $V_{SD}$ | $I_S$ = 1.0A, $V_{GS}$ = 0V | | | 1.2 | V |

1) Pulse test: pulse width <= 300us, duty cycle<= 2%

## Typical ElectricalL and Thermal Characteristics

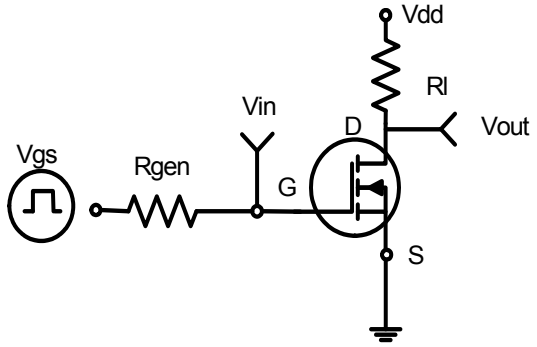



**Figure 1:Switching Test Circuit**

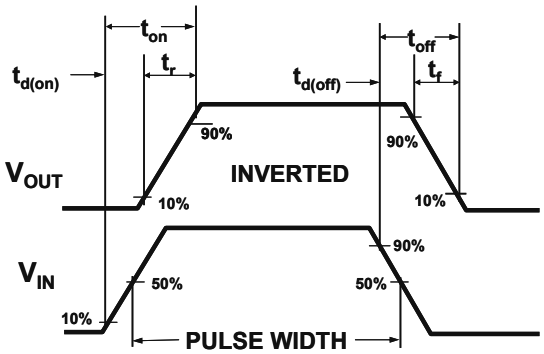



**Figure 2:Switching Waveforms**

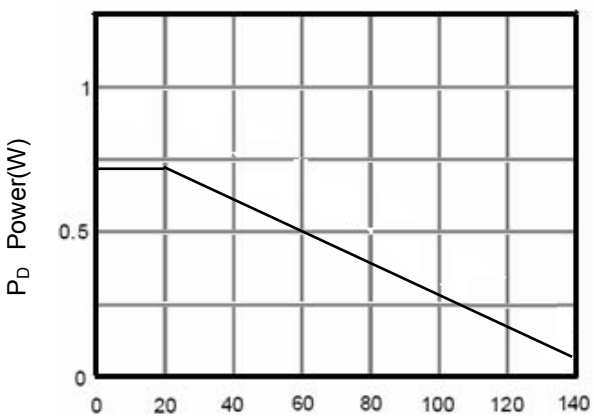



**Figure 3 Power Dissipation**

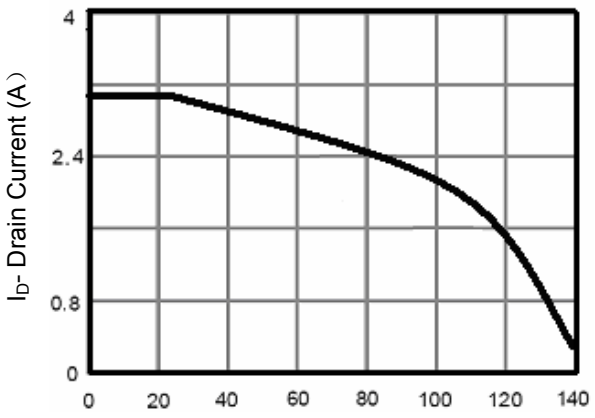



**Figure 4 Drain Current**

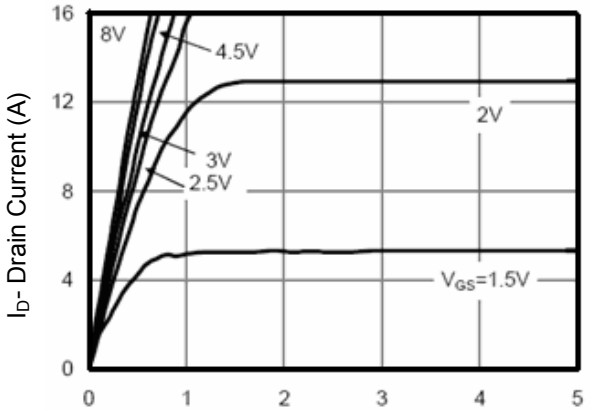



**Figure 5 Output Characteristics**

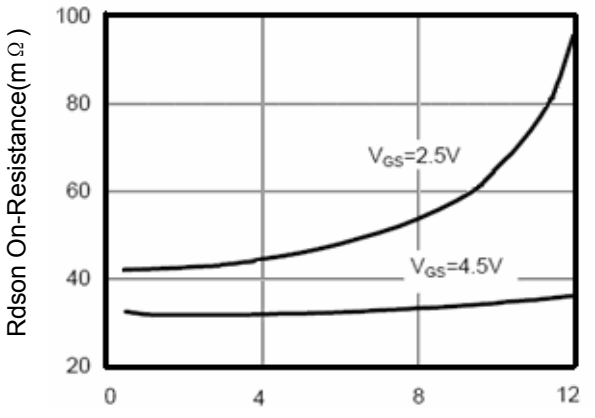



**Figure 6 Drain-Source On-Resistance**

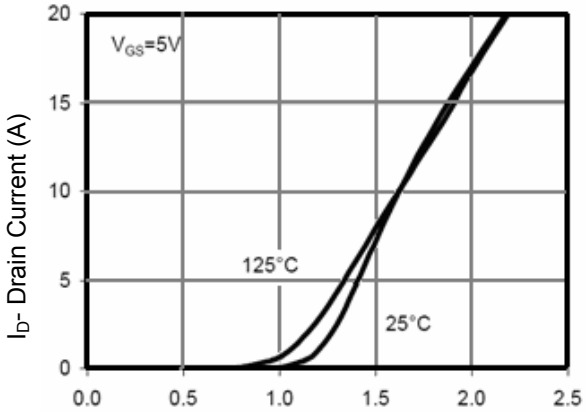



**Figure 7 Transfer Characteristics**

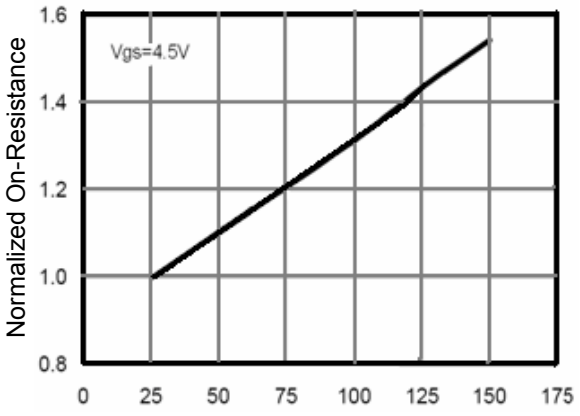



**Figure 8 Drain-Source On-Resistance**

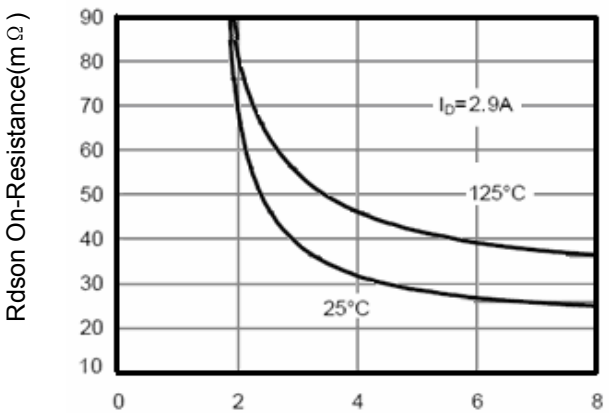



**Figure 9 Rdson vs Vgs**

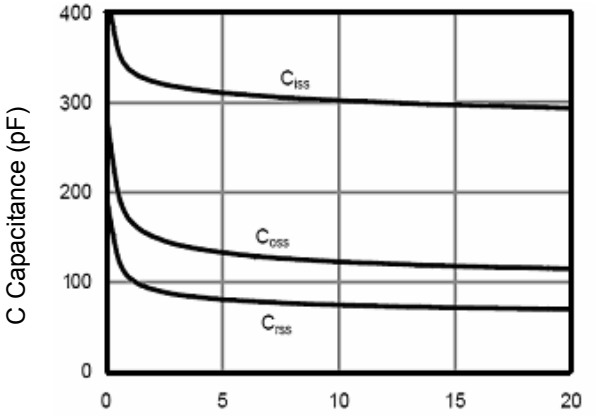



**Figure 10 Capacitance vs Vds**

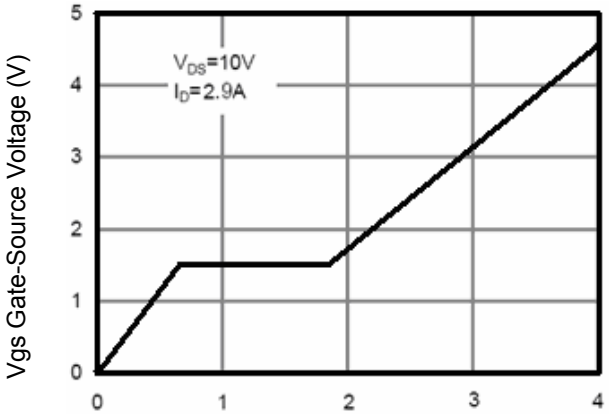



**Figure 11 Gate Charge**

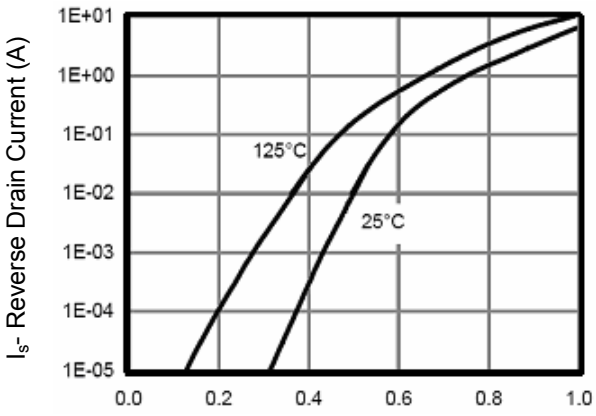



**Figure 12 Source- Drain Diode Forward**